

Title (en)

METHOD FOR THERMALLY TREATING SEMICONDUCTOR SUBSTRATES

Title (de)

VERFAHREN ZUM THERMISCHEN BEHANDELN VON HALBLEITERSUBSTRATEN

Title (fr)

PROCEDE DE TRAITEMENT THERMIQUE DE SUBSTRATS EN SEMI-CONDUCTEUR

Publication

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Application

EP 00979480 A 20000929

Priority

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Abstract (en)

[origin: DE19952015A1] The aim of the invention is to thermally treat objects, especially semiconductor substrates, in a complete and effective manner and in a reaction chamber. According to the inventive method, at least partial areas of the object are heated to at least three temperature peaks, whereby corresponding cooling phases in-between are provided.

IPC 1-7

H01L 21/324

IPC 8 full level

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